

## Vishay Semiconductors

# Molding Type Module IGBT, 1-in-1 Package, 1200 V and 600 A



**Dual INT-A-PAK** 

PRIMARY CHARACTERISTICS						
V <sub>CES</sub>	1200 V					
I <sub>C</sub> at T <sub>C</sub> = 80 °C	600 A					
$V_{CE(on)}$ (typical) at $I_C = 600$ A, 25 °C	1.9 V					
Speed	8 kHz to 30 kHz					
Package	Dual INT-A-PAK					
Circuit configuration	Single switch with AP diode					

#### **FEATURES**

- High short circuit capability, self limiting to 6 x I<sub>C</sub>
- 10 µs short circuit capability
- V<sub>CE(on)</sub> with positive temperature coefficient
- Low inductance case
- · Fast and soft reverse recovery antiparallel FWD
- Isolated copper baseplate using DCB (Direct Copper Bonding) technology
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **TYPICAL APPLICATIONS**

- · AC inverter drives
- Switching mode power supplies
- Electronic welder at fsw up to 20 kHz

#### **DESCRIPTION**

Vishay's IGBT power module provides ultralow conduction loss as well as short circuit ruggedness. It is designed for applications such as inverters and UPS.

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Collector to emitter voltage	V <sub>CES</sub>		1200	V	
Gate to emitter voltage	$V_{GES}$		± 20	ľ	
Collector current at T 150 °C		T <sub>C</sub> = 25 °C	910		
Collector current at T <sub>J</sub> = 150 °C	Ic	T <sub>C</sub> = 80 °C	600	1	
Pulsed collector current	I <sub>CM</sub> <sup>(1)</sup>	T <sub>C</sub> = 80 °C	1200	А	
Diode continuous forward current	I <sub>F</sub>		600	]	
Diode maximum forward current	I <sub>FM</sub>		1200	1	
Maximum power dissipation	P <sub>D</sub>	T <sub>J</sub> = 150 °C	3125	W	
Short circuit withstand time	t <sub>SC</sub>	T <sub>J</sub> = 125 °C	10	μs	
RMS isolation voltage	V <sub>ISOL</sub>	f = 50 Hz, t = 1 min	2500	V	
I <sup>2</sup> t-value, diode	l <sup>2</sup> t	V <sub>R</sub> = 0 V, t = 10 ms, T <sub>J</sub> = 125 °C	74 000	A <sup>2</sup> s	

#### Note

<sup>(1)</sup> Repetitive rating: pulse width limited by maximum junction temperature.

IGBT ELECTRICAL SPECIFICATIONS (T <sub>C</sub> = 25 °C unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Collector to emitter breakdown voltage	V <sub>(BR)CES</sub>	T <sub>J</sub> = 25 °C	1200	-	-		
Collector to emitter voltage	V	V <sub>GE</sub> = 15 V, I <sub>C</sub> = 600 A, T <sub>J</sub> = 25 °C	-	1.9	-	V	
	V <sub>CE(on)</sub>	V <sub>GE</sub> = 15 V, I <sub>C</sub> = 600 A, T <sub>J</sub> = 125 °C	-	2.1	-		
Gate to emitter threshold voltage	V <sub>GE(th)</sub>	$V_{CE} = V_{GE}$ , $I_C = 24$ mA, $T_J = 25$ °C	5.0	6.2	7.0		
Collector cut-off current	I <sub>CES</sub>	$V_{CE} = V_{CES}$ , $V_{GE} = 0$ V, $T_{J} = 25$ °C	-	-	5.0	mA	
Gate to emitter leakage current	I <sub>GES</sub>	$V_{GE} = V_{GES}$ , $V_{CE} = 0$ V, $T_{J} = 25$ °C	-	-	400	nA	



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SWITCHING CHARACTERISTICS	3					
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS		TYP.	MAX.	UNITS
Turn-on delay time	t <sub>d(on)</sub>		-	200	-	ns mJ
Rise time	t <sub>r</sub>	1	-	62	-	
Turn-off delay time	t <sub>d(off)</sub>	$V_{CC} = 600 \text{ V}, I_{C} = 600 \text{ A}, R_{g} = 3 \Omega,$	-	510	-	
Fall time	t <sub>f</sub>	$V_{GE} = \pm 15 \text{ V}, T_{J} = 25 \text{ °C}$	-	60	-	
Turn-on switching loss	E <sub>on</sub>	1	-	39	-	
Turn-off switching loss	E <sub>off</sub>	1	-	48	-	
Turn-on delay time	t <sub>d(on)</sub>		-	210	-	- ns
Rise time	t <sub>r</sub>		-	65	-	
Turn-off delay time	t <sub>d(off)</sub>	$V_{CC} = 600 \text{ V}, I_{C} = 600 \text{ A}, R_{g} = 3 \Omega,$	-	600	-	
Fall time	t <sub>f</sub>	$V_{GE} = \pm 15 \text{ V}, T_{J} = 125 \text{ °C}$	-	75	-	
Turn-on switching loss	E <sub>on</sub>		-	45	-	mJ
Turn-off switching loss	E <sub>off</sub>		-	60	-	IIIJ
Input capacitance	C <sub>ies</sub>		-	41.0	-	
Output capacitance	C <sub>oes</sub>	$V_{GE} = 0 \text{ V}, V_{CE} = 25 \text{ V}, f = 1.0 \text{ MHz}$	-	3.1	-	nF
Reverse transfer capacitance	C <sub>res</sub>		-	2.0	-	
SC data	I <sub>SC</sub>	$t_{SC} \leq 10 \; \mu s,  V_{GE} = 15 \; V,  T_J = 25 \; ^{\circ}C, \\ V_{CC} = 900 \; V,  V_{CEM} \leq 1200 \; V$	-	2600	-	А
Stray inductance	L <sub>CE</sub>		-	-	20	nH
Module lead resistance, terminal to chip	R <sub>CC'+EE'</sub>	T <sub>C</sub> = 25 °C	-	0.18	-	mΩ

<b>DIODE ELECTRICAL SPECIFICATIONS</b> (T <sub>C</sub> = 25 °C unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDIT	TEST CONDITIONS		TYP.	MAX.	UNITS
Diode forward voltage	V <sub>F</sub>	I <sub>F</sub> = 600 A	T <sub>J</sub> = 25 °C	-	1.8	2.4	V
			T <sub>J</sub> = 125 °C	-	1.9	-	
Diode reverse recovery charge	Q <sub>rr</sub>	$I_F = 600 \text{ A}, V_R = 600 \text{ V},$ $dI_F/dt = -6000 \text{ A/}\mu\text{s},$ $V_{GF} = -15 \text{ V}$	T <sub>J</sub> = 25 °C	-	65	-	0
			T <sub>J</sub> = 125 °C	-	100	-	μC
Diede peek verreure vereurent	I <sub>rr</sub>		T <sub>J</sub> = 25 °C	-	450	-	^
Diode peak reverse recovery current			T <sub>J</sub> = 125 °C	-	510		A
Diode reverse recovery energy	E <sub>rec</sub>		T <sub>J</sub> = 25 °C	-	35	-	m l
			T <sub>J</sub> = 125 °C	-	42	-	mJ

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Operating temperature rang	ge	TJ		-40	-	150	°C
Storage temperature range		T <sub>Stg</sub>		-40	-	125	°C
Junction to case	IGBT	В		-	-	0.04	
per module	Diode	R <sub>thJC</sub>		-	-	0.09	K/W
Case to sink		R <sub>thCS</sub>	Conductive grease applied	-	0.035	-	
Mounting torque			Power terminal screw: M6	2.5 to 5.0		Nm	
			Mounting screw: M6	3.0 to 6.0		INITI	
Weight				310		g	



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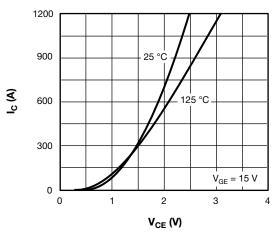


Fig. 1 - Typical Output Characteristics

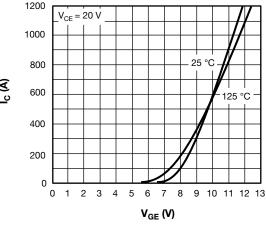


Fig. 2 - Typical Transfer Characteristics

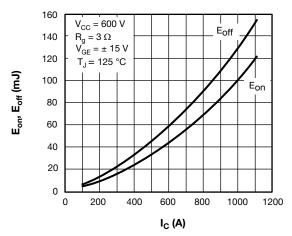


Fig. 3 - Switching Loss vs. Collector Current

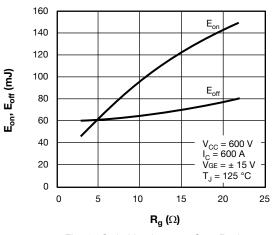


Fig. 4 - Switching Loss vs. Gate Resistor

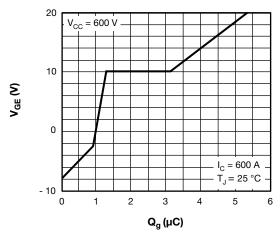


Fig. 5 - Gate Charge Characteristics

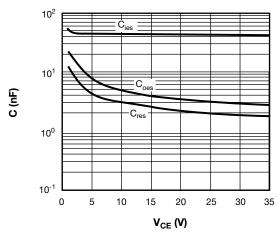


Fig. 6 - Typical Capacitance vs. Collector-Emitter Voltage



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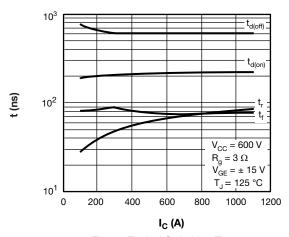


Fig. 7 - Typical Switching Times

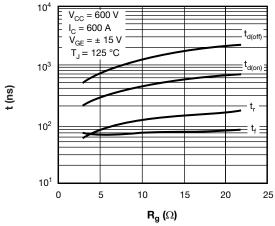


Fig. 8 - Typical Switching Times vs. Gate Resistance Rq

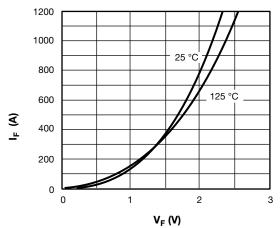


Fig. 9 - Typical forward Characteristics (Diode)

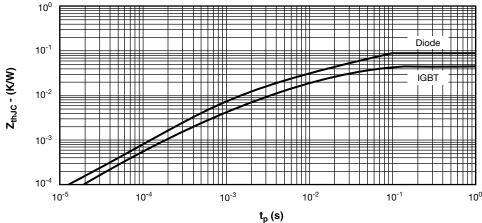
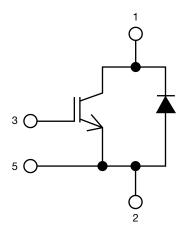


Fig. 10 - Transient Thermal Impedance



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## **CIRCUIT CONFIGURATION**



LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95526			



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